Inventor:

Luan C. Tran

Title:

Methods of Forming Semiconductor Constructions

Assignee:

Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/364,054, filed February 10, 2003. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated:

Rv.

Talan:

Taylor,

Reg. Nø

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Form PTO-1449			U.S. PATÉ	DEPARTMENT OF COMMERCE ENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2357		priori 10/36	priority SERIAL NO. 10/364.054	
LIST OF ART CITED B (Use several sheets if					APPLICANT Luan C. Tran				
			priority Fil. February 10		priority FILING DA February 10, 2003	ATE priority GRO		ity GROUP	
U.S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
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	AM								
	AN					<u> </u>			
	AO								
OTHER REFERENCES (including Author, Title, Datc, Pertinent Pages, Etc.)									
	ΛQ	Young et al., "A 0.13 μm CMOS Technology with 193 nm Lithography and Cu/Low-k for High Performance Applications", 1EDM, pgs. 563-566, April 2000.							
									
	AR	Ych et al., "Optimum Halo Structure for Sub-0.1 μm CMOSFETs", IEEE Transactions on Electronic Devices, Vol. 48, No. 10, October 2001, pgs. 2357-2362.							
	AS	Bouillon et al., "Re-examination of Indium implantation for a low power 0.1 µm technology", IDEM, pgs. 897-900, 1995 (year is sufficient so that date is not in issue).							
							·		
EXAMINER			DATE CONSIDER	DATE CONSIDERED					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									